

MA856

Silicon epitaxial planer type

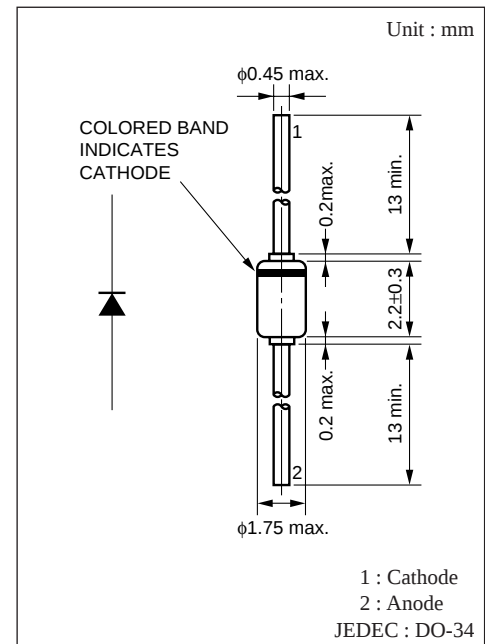
For band switching

■ Features

- Extra-small DHD envelope, enabling 5mm pitch insertion
- Less voltage dependence of the capacity C_t between pins
- Low forward dynamic resistance r_f
- Optimum for a band switching of tuner

■ Absolute Maximum Ratings (Ta= 25°C)

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	35	V
Forward current (DC)	I_F	100	mA
Operating ambient temperature	T_{opr}	– 25 to + 85	°C
Storage temperature	T_{stg}	– 55 to +150	°C



■ Electrical Characteristics (Ta= 25°C)

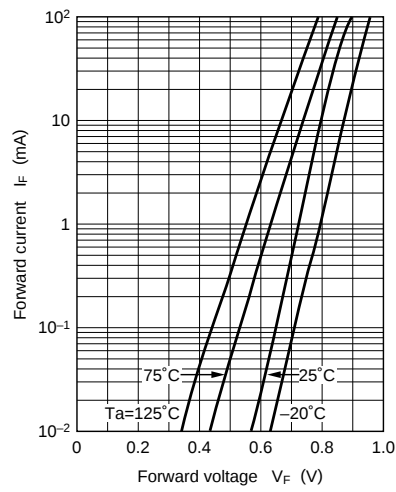
Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R *	$V_R = 33V$			100	nA
Forward voltage (DC)	V_F	$I_F = 100mA$			1	V
Terminal capacitance	C_D	$V_R = 15V, f = 1MHz$			2	pF
Forward dynamic resistance	r_f	$I_F = 3mA, f = 100MHz$			0.85	Ω

Note 1 : Rated input/output frequency : 100MHz
2 : * Measurement with the beam shielded

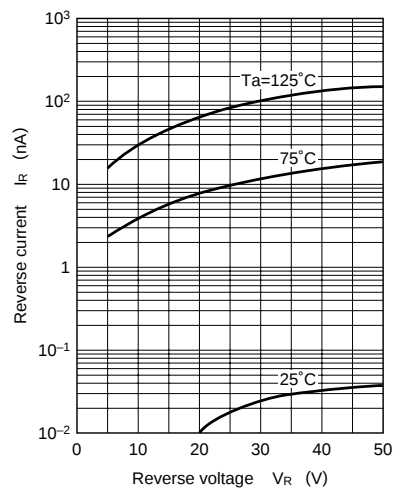
■ Cathode Indication

Type No.	MA856
Color	Yellow

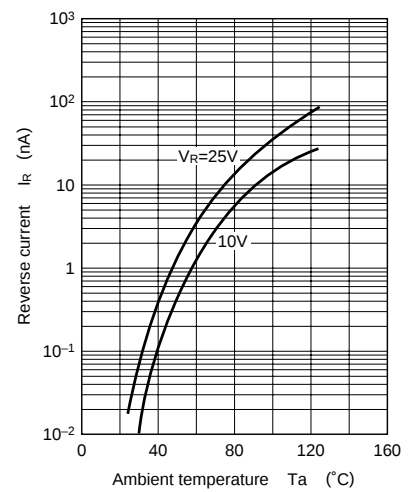
$I_F - V_F$



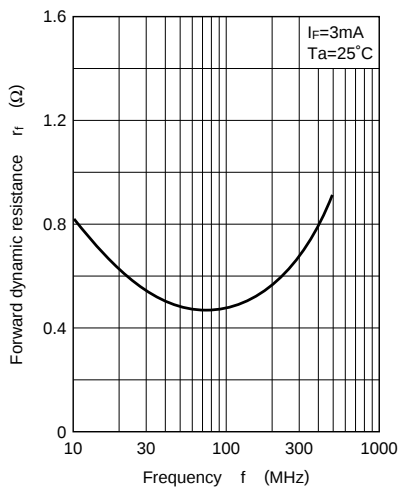
$I_R - V_R$



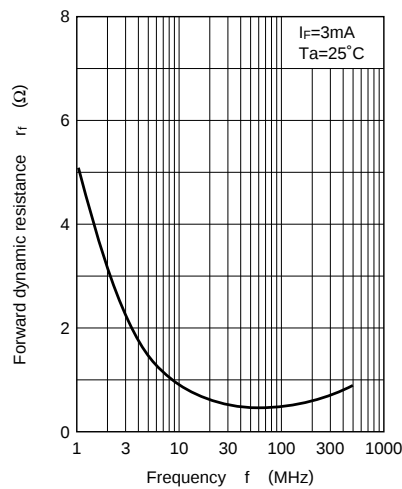
$I_R - T_a$



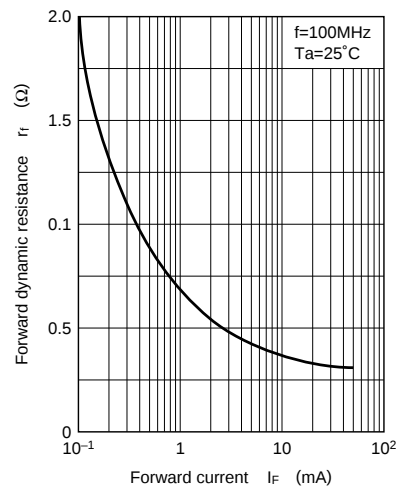
$r_f - f$



$r_f - f$



$r_f - I_F$



$C_t - V_R$

